

2SD1408

SILICON NPN TRIPLE DIFFUSED TYPE

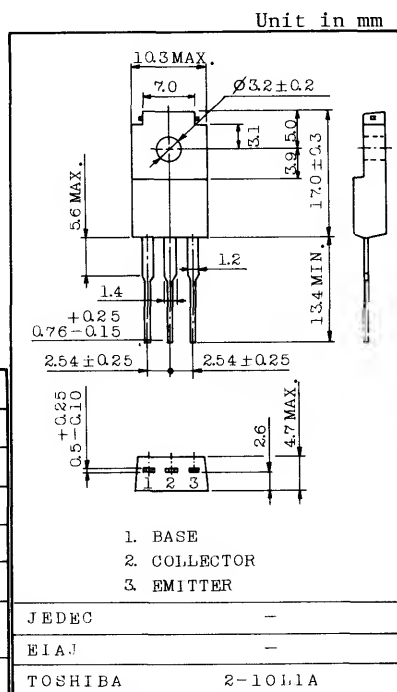
POWER AMPLIFIER APPLICATIONS.

FEATURES:

- High Power Dissipation : $P_C=25W$ ($T_C=25^{\circ}C$)
- Good Linearity of h_{FE}
- Complementary to 2SB1017
- Recommended for 20~25W High Fidelity Audio Frequency Amplifier Output Stage.

MAXIMUM RATINGS ($T_a=25^{\circ}C$)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	80	V
Collector-Emitter Voltage	V_{CEO}	80	V
Emitter-Base Voltage	V_{EBO}	5	V
Collector Current	I_C	4	A
Base Current	I_B	0.4	A
Collector Power Dissipation ($T_C=25^{\circ}C$)	P_C	25	W
Junction Temperature	T_j	150	$^{\circ}C$
Storage Temperature Range	T_{stg}	-55~150	$^{\circ}C$



Weight : 2.1g

ELECTRICAL CHARACTERISTICS ($T_a=25^{\circ}C$)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	$V_{CB}=80V, I_E=0$	-	-	30	μA
Emitter Cut-off Current	I_{EBO}	$V_{EB}=5V, I_C=0$	-	-	100	μA
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C=50mA, I_B=0$	80	-	-	V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E=10mA, I_C=0$	5	-	-	V
DC Current Gain	$h_{FE(1)}$ (Note)	$V_{CE}=5V, I_C=0.5A$	40	-	240	
	$h_{FE(2)}$	$V_{CE}=5V, I_C=3A$	15	50	-	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=3A, I_B=0.3A$	-	0.45	1.5	V
Base-Emitter Voltage	V_{BE}	$V_{CE}=5V, I_C=3A$	-	1.0	1.5	V
Transition Frequency	f_T	$V_{CE}=5V, I_C=0.5A$	-	8.0	-	MHz
Collector Output Capacitance	C_{ob}	$V_{CB}=10V, I_E=0, f=1MHz$	-	90	-	pF

Note : $h_{FE(1)}$ Classification R : 40~80, O : 70~140, Y : 120~240

TOSHIBA CORPORATION

